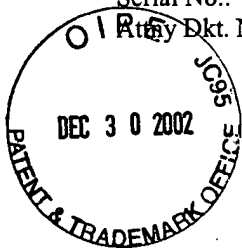


Inventor: Kennedy et al.
Serial No.: 09/547,167
Att. Dkt. No. 100595.0052US1

Art Unit: 2822
Examiner: C. Novacek



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
WASHINGTON, D.C. 20231

#12
#12/12/03
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Inventor: **Kennedy et al.**
Serial No: **09/547,167**
Filed: **April 11, 2000**
For: **The Use of Sacrificial
Inorganic Dielectrics for
Dual Damascene Processes
Utilizing Organic Intermetal
Dielectrics**

Examiner: C. Novacek
Art Unit: 2822

Attorney Docket No.: 100595.0052US1

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OFFICE OF PETITIONS

PRELIMINARY AMENDMENT

IN THE CLAIMS

Please find below a Clean Copy of Claims for Examiner's Immediate Reference. A Marked Up Copy and Additional Clean Copy are herein attached.

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1. (Twice Amended) A method of making conducting vias and conducting lines on a substrate comprising:
- depositing a stack having a top surface on a substrate, wherein the stack comprises a first organic intermetal dielectric layer and a hardmask layer, wherein the hardmask layer comprises a material comprising silicon oxynitride or silicon oxide;
- forming a via opening in said stack;
- depositing a sacrificial inorganic dielectric in the via opening, wherein the sacrificial inorganic dielectric substantially filling the via opening and substantially covering the top surface of the stack;